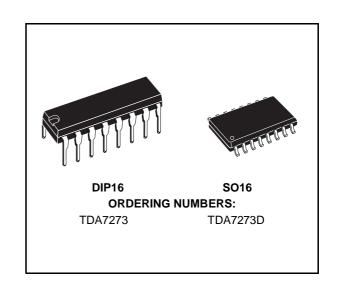


SINGLE CHIP STEREO CASSETTE PLAYBACK SYSTEM

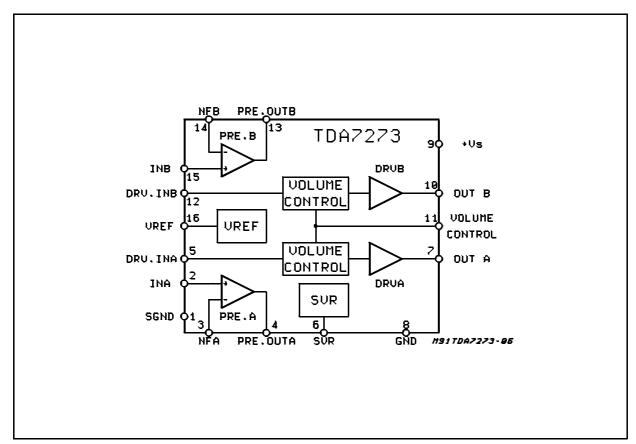
- WIDE OPERATING SUPPLY VOLTAGE (1.8V to 7V)
- INPUT COUPLING WITHOUT CAPACITORS
- BUILT-IN DC STEREO VOLUME CONTROL
- BUILT-IN RIPPLE FILTERS
- LOW QUIESCENT CURRENT
- NO EXTERNAL BOUCHEROT CELL
- MAX OUTPUT CURRENT 70mA PEAK

DESCRIPTION

The TDA7273 is a monolithic integrated circuit designed for portable cassette players market. It comprises preamplifiers, DC volume control, and headphone drivers.



BLOCK DIAGRAM



September 2003 1/9

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Test Conditions	Unit
Vs	Supply Voltage	9	V
Io	Output Current (max)	70	mA
T _{op}	Operating Temperature Range	-20 to 70	°C
T _{stg} , T _j	Storage & Junction Temperature Range	-40 to +150	°C

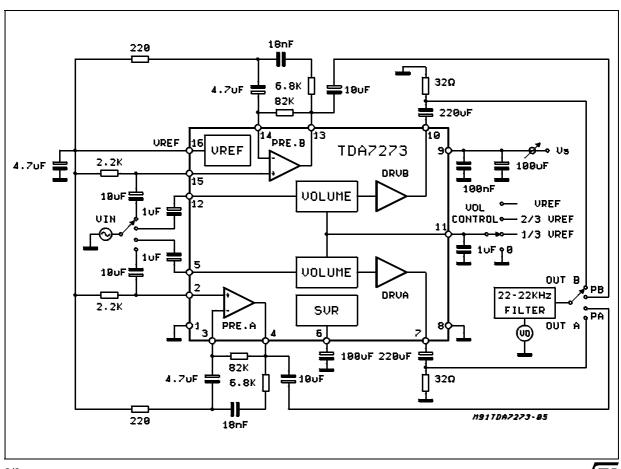
THERMAL DATA

Symbol	Description	DIP-16	SO-16	Unit
R _{thj-amb}	Thermal Resistance Junction-ambient Max	100	200	°C/W

DC CHARACTERISTICS: $T_{amb} = 25^{\circ}C$; $V_S = 3V$; $R_L = 10K\Omega$ (Preamplifier), $R_L = 32\Omega$ (Headphone); $V_{IN} = 0$; V_{OL} control = V_{ref}

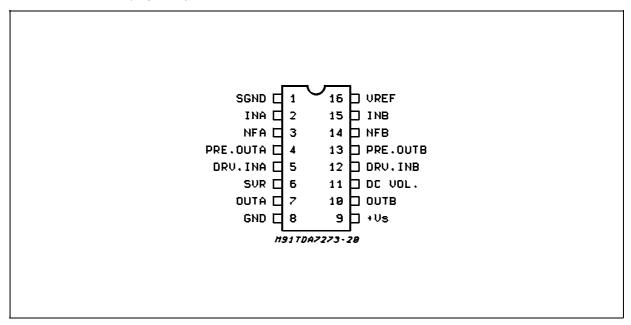
Terminal No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
Terminal Voltage (V)	0	1.5	1.5	1.5	1.5	2.7	1.5	0	3	1.5	1.5	1.5	1.5	1.5	1.5	1.5

TEST CIRCUIT



2/9

PIN CONNECTION (Top view)



ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $V_{S} = 3V$, f = 1KHz, $R_{L} = 32\Omega$ Vol. control = $2/3V_{ref}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Vs	Supply Voltage		1.8		7	V
I _d	Quiescent Current			14	20	mA
Vref	Reference Voltage		1.3	1.49	1.7	V

PREAMPLIFIER SECTION

G _{VO}	Open Loop Gain			70		dB
Gv	Close Loop Gain		30	33	35	dB
Vo	Output Voltage	THD = 1%	600	850		mV
l _b	Bias Current			3		μΑ
THD	Total Harmonic Distortion	V _o = 330mVrms		0.05	0.25	%
C_{t}	Cross Talk	Rg = $2.2K\Omega$; V _o = 330 mVrms		74		dB
E _N	Output Noise	Rg = 2.2 K Ω ; BW = 22 Hz to 22 KHz		100		μV
SVR	Ripple Rejection	$\begin{aligned} R_g &= 2.2 \text{K}\Omega \ \text{V}_R = 100 \text{mVrms} \\ \text{f} &= 100 \text{Hz}; \ \text{C}_{\text{SVR}} = 100 \mu \text{F} \end{aligned}$	40	50		dB

HEADPHONE DRIVER

V _{o(DC)}	DC Output Voltage			1.50		V
Po	Output Power	THD = 10%;	15	30		mW
Po	Transient Output Power	THD = 10% RL = 16Ω		50		mW
G_V	Close Loop Gain	P _o = 5mW	28	31	34	dB
THD	Total Harmonic Distortion	P _o = 5mW		0.2	1	%
Ct	Cross Talk	$Rg = 10K\Omega$; $P_0 = 5mW$	40	50		dB
SVR	Ripple Rejection	V_r = 100mVrms, f = 100Hz Vol. control = 1/3V _{ref} C_{SVR} = 100 μ F; R_g =600 Ω		47		dB
	Volume Control Range		66	75		dB

Figure 1: Application Circuit

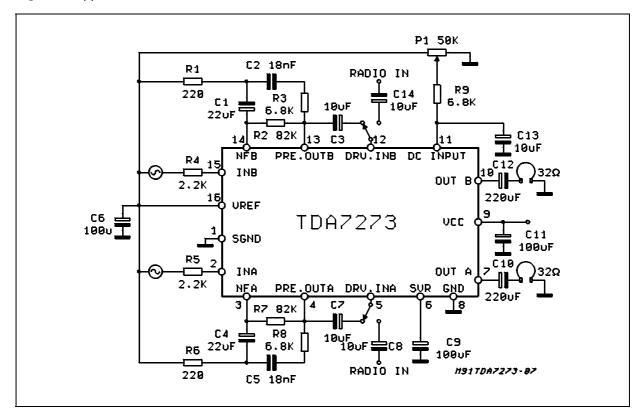


Figure 2: P.C. Board and Component Layout of the Circuit of Figure 1 (1:1 scale)

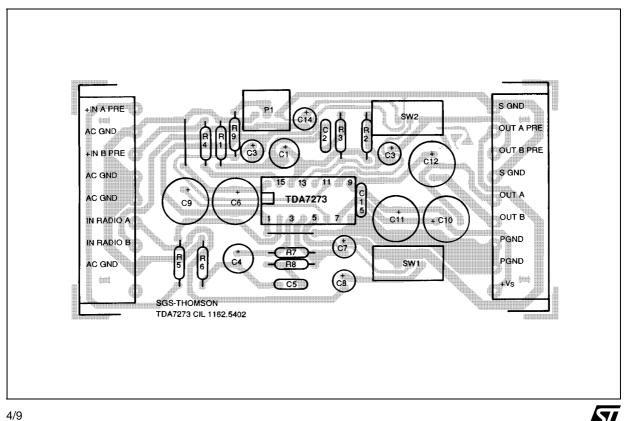


Figure 3: Supply Current vs. Supply Voltage (Preamplifier + Driver)

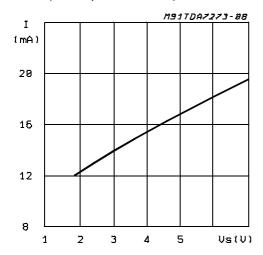


Figure 5: Closed Loop Gain vs. Frequency $(V_S = 3V)$ (PREAMPLIFIER)

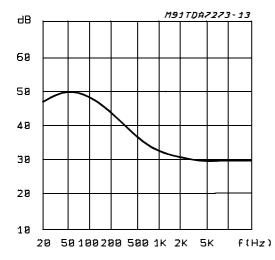


Figure 7: SVR vs. Frequency (PREAMPLIFIER)

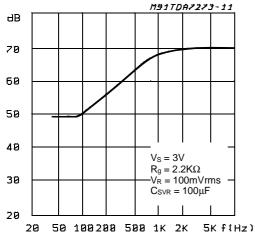


Figure 4: V_{ref}, vs. Supply Voltage (pin 16)

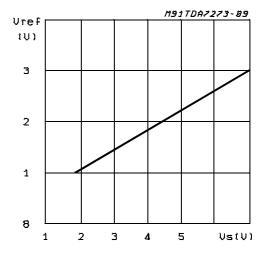


Figure 6: THD vs. Frequency ($V_S = 3V$, $V_o = 330 \text{mVrms}$, $R_L = 10 \text{K}\Omega$) (PREAMPLIFIER)

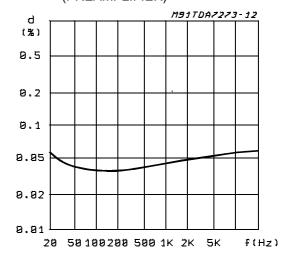


Figure 8: Quiescent Output Voltage vs. Supply Voltage (DRIVER)

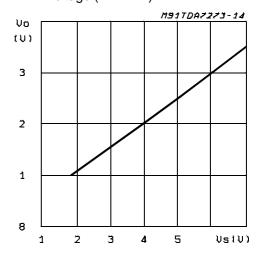


Figure 9: Closed Loop Gain vs Frequency $(V_S = 3V, R_L = 32\Omega)$ (DRIVER)

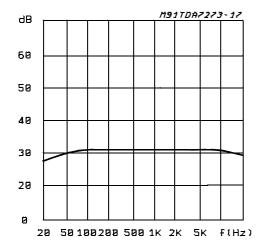


Figure 11: THD vs. Output Power ($V_0 = 2/3V_{ref}$, $V_S = 3V$, $R_L = 32\Omega$, f = 1KHz) (DRIVER)

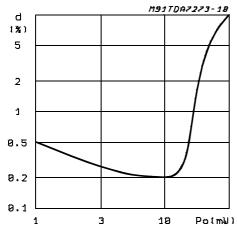


Figure 13: SVR vs. Frequency $V_S = 3V$ ($R_L = 32\Omega$, $V_r = 100Vrms$ $R_g = 600\Omega$, $C_{SVR} = 100mV$) (DRIVER)

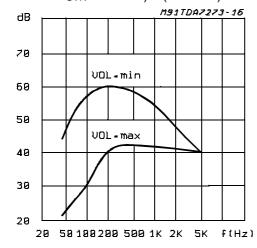


Figure 10: Output Power vs. Supply Voltage (Vol = $2/3V_{ref}$, $R_L = 32\Omega$, THD = 10%, f = 1KHz) (DRIVER)

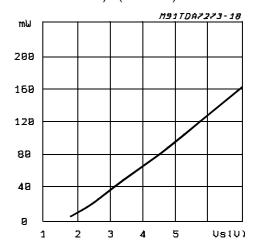


Figure 12: THD vs. Frequency ($P_0 = 5mW$, $V_S = 3V R_L = 32\Omega$) (DRIVER)

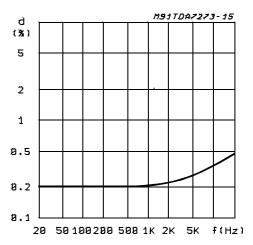
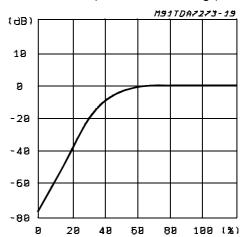
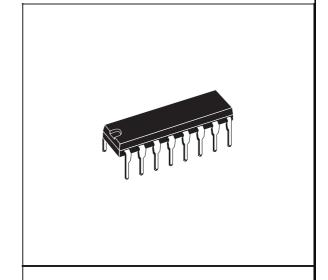


Figure 14: Volume Control (0dB = 10mW, $V_S = 3V R_{Vol} = 50K\Omega$, $R_L = 32\Omega$, f = 1KHz) vs. Volume Setting (DRIVER)

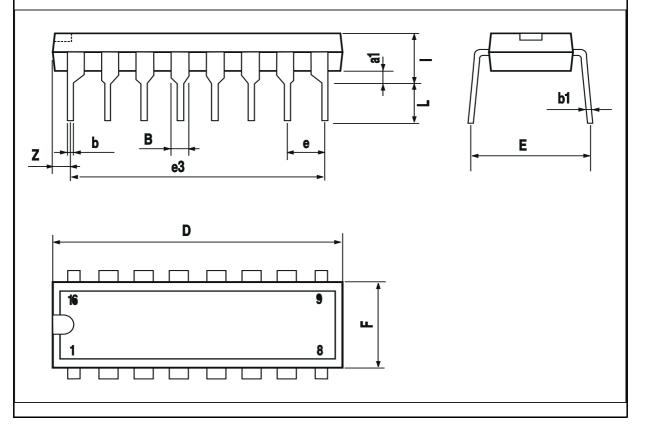


		mm		inch					
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
a1	0.51			0.020					
В	0.77		1.65	0.030		0.065			
b		0.5			0.020				
b1		0.25			0.010				
D			20			0.787			
Е		8.5			0.335				
е		2.54			0.100				
e3		17.78			0.700				
F			7.1			0.280			
ı			5.1			0.201			
L		3.3			0.130				
Z			1.27			0.050			

OUTLINE AND MECHANICAL DATA

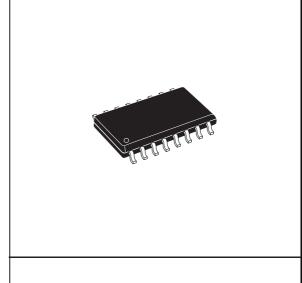


DIP16

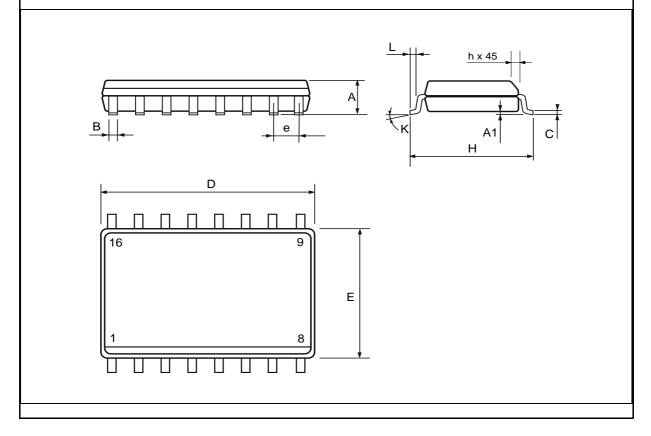


				ı					
DIM.		mm		inch					
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
Α	2.35		2.65	0.093		0.104			
A1	0.1		0.3	0.004		0.012			
В	0.33		0.51	0.013		0.020			
С	0.23		0.32	0.009		0.013			
D	10.1		10.5	0.398		0.413			
E	7.4		7.6	0.291		0.299			
е		1.27			0.050				
Н	10		10.65	0.394		0.419			
h	0.25		0.75	0.010		0.030			
L	0.4		1.27	0.016		0.050			
К	0° (min.)8° (max.)								

OUTLINE AND MECHANICAL DATA



SO16 Wide



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